

FIG. 2

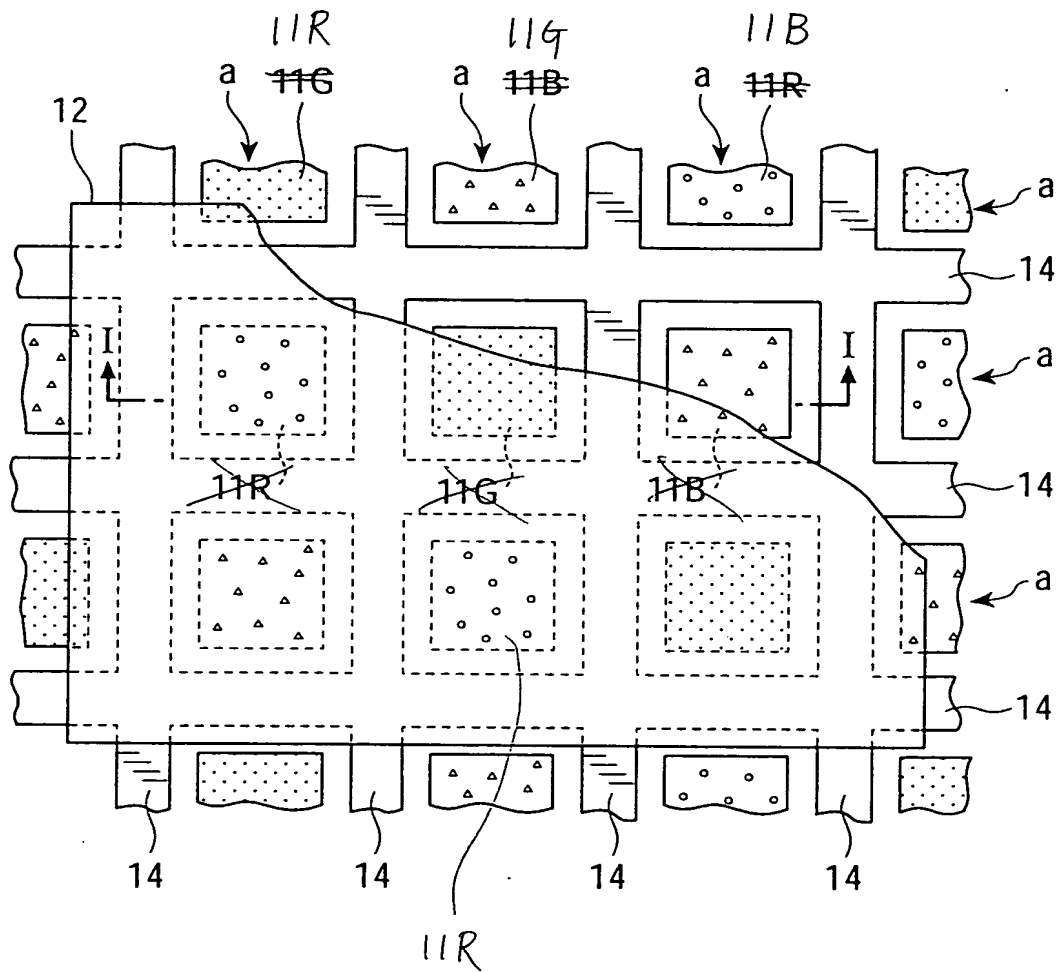


FIG. 3A

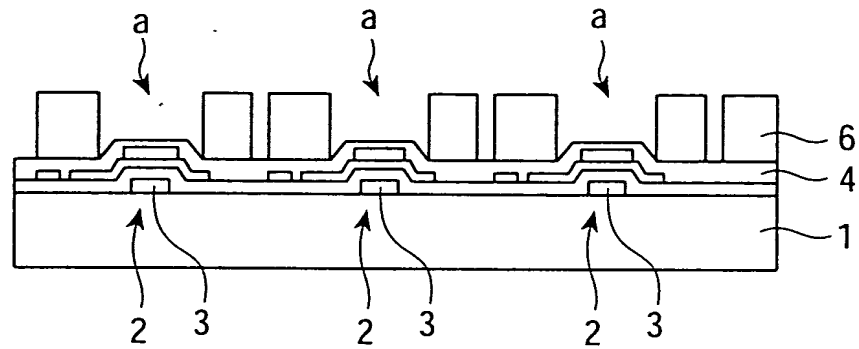


FIG. 3B

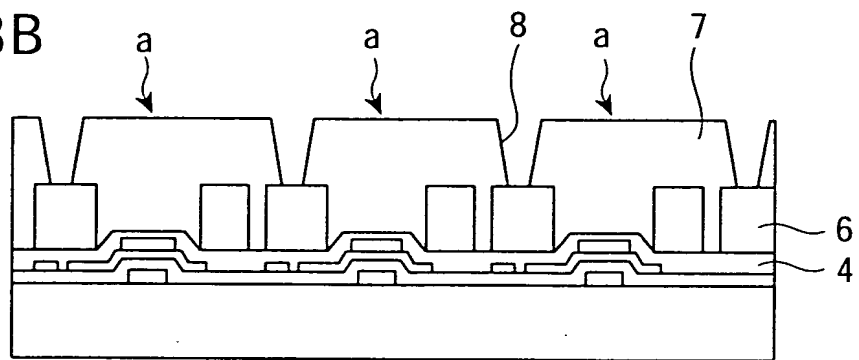


FIG. 3C

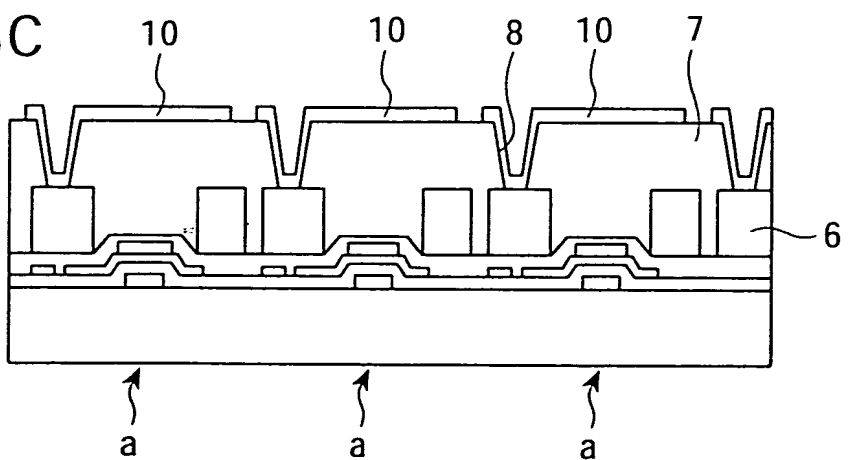
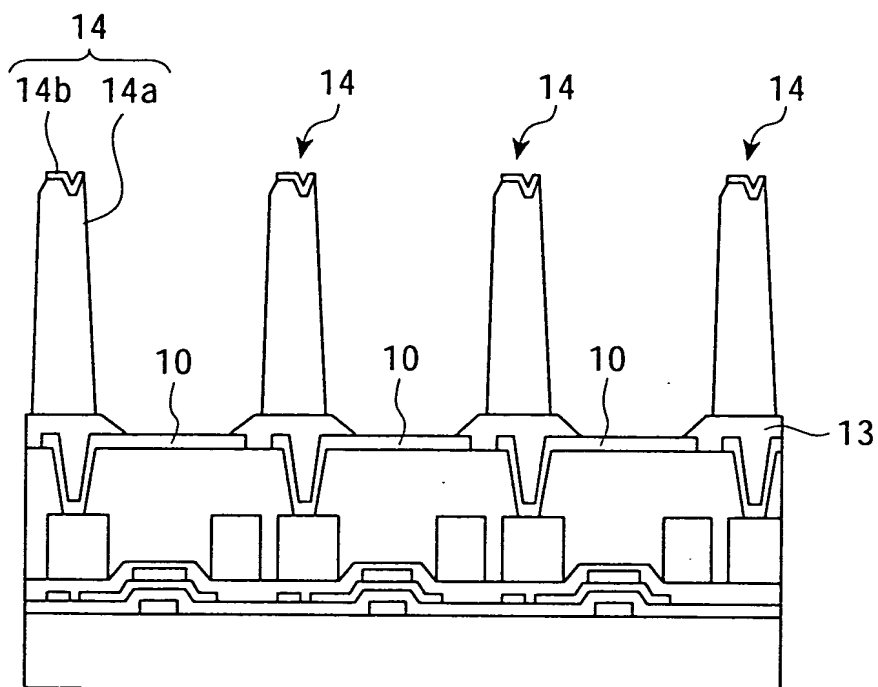


FIG. 4



0042307 6666560

FIG. 5A

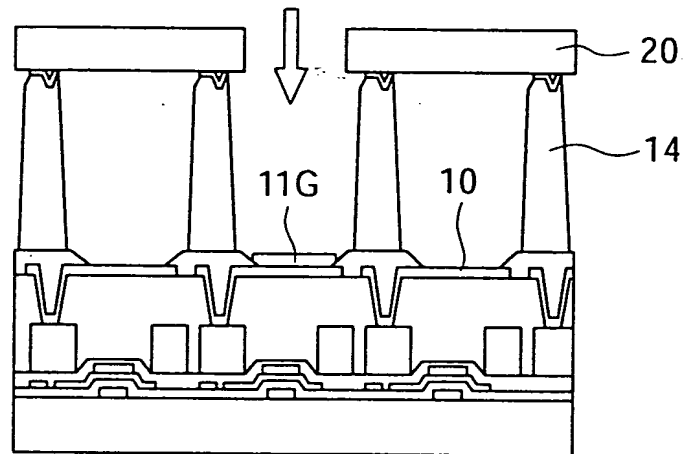


FIG. 5B

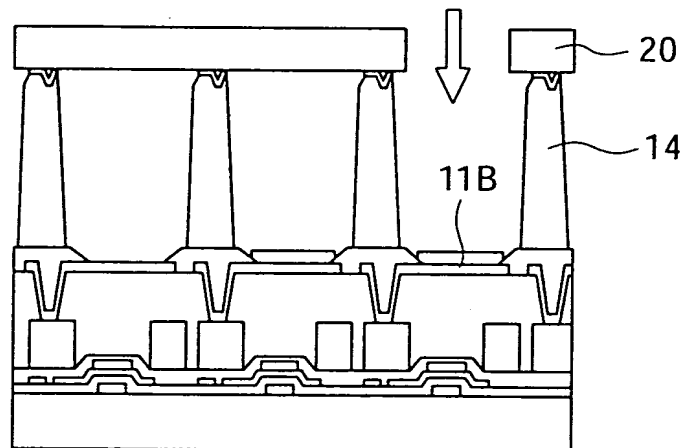
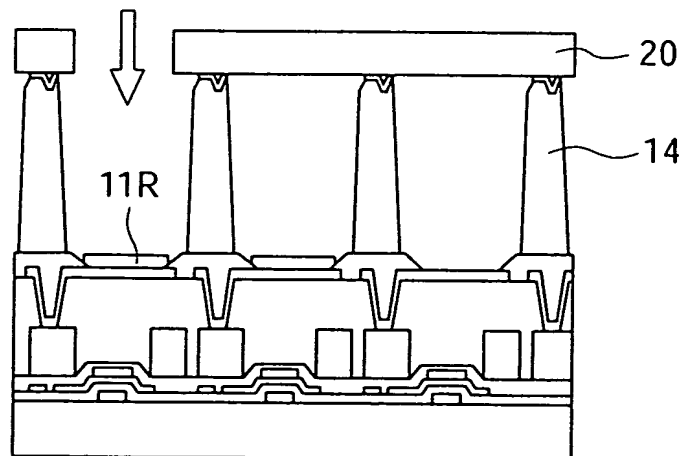


FIG. 5C



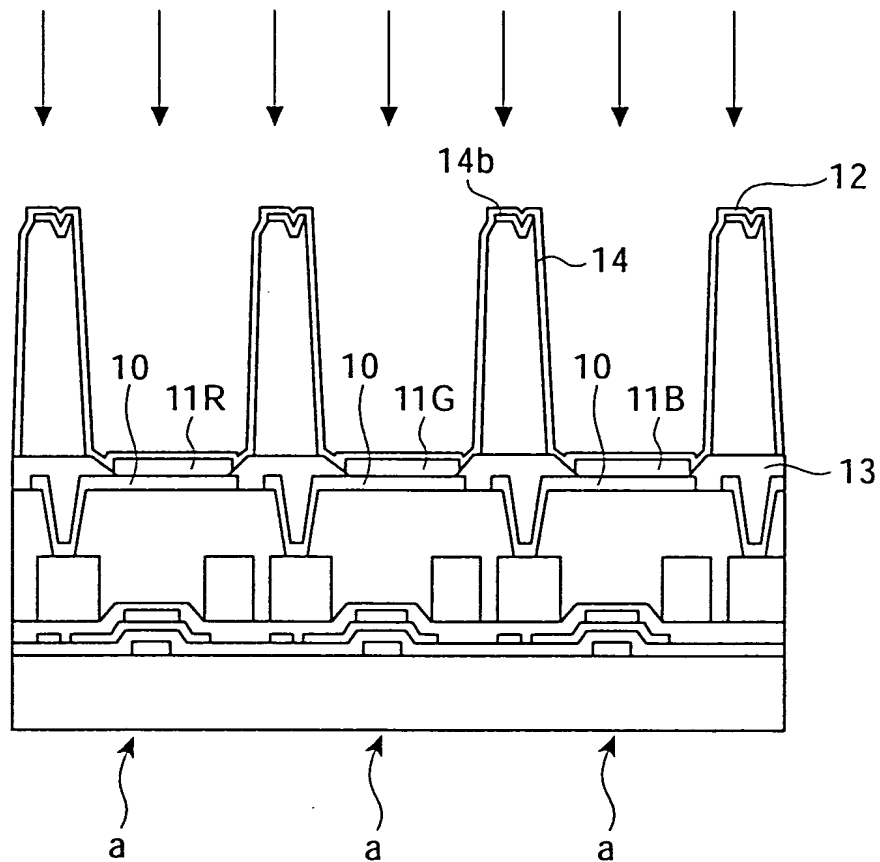
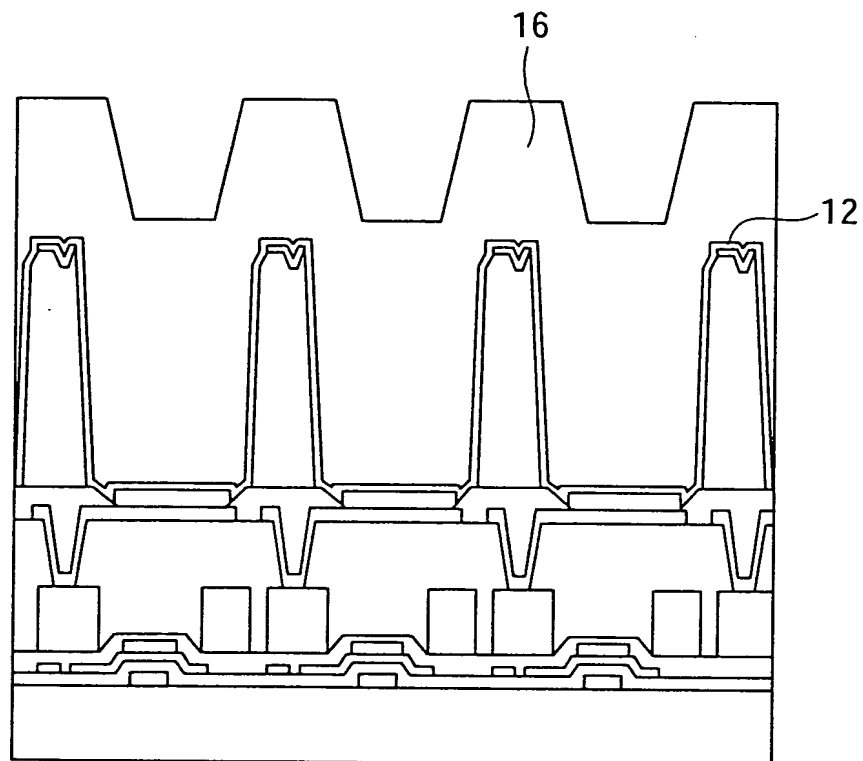
[illegible]

FIG. 7



A cross-sectional view of a semiconductor device. A substrate 12 is shown at the bottom. A base layer 14 is formed on the substrate. The base layer 14 is divided into two regions: 14a, which is a trapezoidal shape, and 14b, which is a rectangular shape. The regions 14a and 14b are separated by a vertical boundary. The top surface of the base layer 14 is indicated by a bracket labeled 14.



FIG. 9

